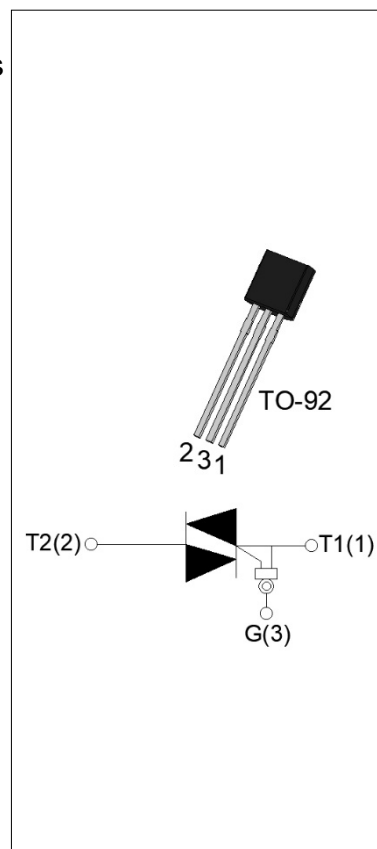


JPTT01U-800SW 1A TRIAC

Rev.A.2.1

DESCRIPTION:

The JPTT01U-800SW triac is suitable for general purpose AC switching. It can be used as an ON/OFF function in applications such as heating regulation, induction motor starting circuits, for phase control operation in light dimmers, motor speed controllers. The JPTT01U-800SW embeds a TVS structure to absorb the inductive turn-off energy such as those described in the IEC 61000-4-5 standards. At the same time, the triac shields the positive signal trigger to reduce the probability of product misoperation. It is triggered with a negative gate current flowing out of the gate pin. Package TO-92 is RoHS compliant.


MAIN FEATURES

Symbol	Value	Unit
$I_{T(RMS)}$	1	A
V_{DRM}/V_{RRM}	800	V
$I_{GT\ II/III}$	10/10	mA

ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Storage junction temperature range	T_{stg}	-40-150	°C
Operating junction temperature range	T_j	-40-125	°C
Repetitive peak off-state voltage ($T_j=25^{\circ}C$)	V_{DRM}	800	V
Repetitive peak reverse voltage ($T_j=25^{\circ}C$)	V_{RRM}	800	V
RMS on-state current ($T_c \leq 53^{\circ}C$)	$I_{T(RMS)}$	1	A
Non repetitive surge peak on-state current (full cycle , $t_p=20ms$, $T_j=25^{\circ}C$)	I_{TSM}	14	A
Non repetitive surge peak on-state current (full cycle , $t_p=16.6ms$, $T_j=25^{\circ}C$)		15.4	
I^2t value for fusing ($t_p=10ms$, $T_j=25^{\circ}C$)	I^2t	0.98	A ² s
Critical rate of rise of on-state current ($I_G=2 \times I_{GT}$, $f=100Hz$, $T_j=125^{\circ}C$)	di/dt	100	A/ μs
Peak gate current ($t_p=20\mu s$, $T_j=125^{\circ}C$)	I_{GM}	1	A
Positive applied gate voltage	V_{GM}	15	V

Average gate power dissipation ($T_j=125^{\circ}\text{C}$)	$P_{G(AV)}$	0.1	W
Peak gate power	P_{GM}	2	W
Peak pulse voltage ($T_j=25^{\circ}\text{C}$; non-repetitive, off-state; FIG.7)	V_{pp}	2.5	kV

ELECTRICAL CHARACTERISTICS ($T_j=25^{\circ}\text{C}$ unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
I_{GT}	$V_D=12\text{V } R_L=33\Omega$	II-III	MAX.	10	mA
V_{GT}		II-III	MAX.	1.3	V
V_{GD}	$V_D=V_{DRM} T_j=125^{\circ}\text{C}$ $R_L=3.3\text{k}\Omega$	II-III	MIN.	0.15	V
I_L	$I_G=1.2I_{GT}$	II	MAX.	40	mA
		III		20	
I_H	$I_T=100\text{mA}$		MAX.	20	mA
dV/dt	$V_D=540\text{V}$ Gate Open $T_j=125^{\circ}\text{C}$		MIN.	1000	$\text{V}/\mu\text{s}$
$(dI/dt)_c$	$(dV/dt)_c=15\text{V}/\mu\text{s}$, $T_j=125^{\circ}\text{C}$		MIN.	2	A/ms
t_{on}	$I_G=20\text{mA } I_A=200\text{mA } I_R=20\text{mA}$ $T_j=25^{\circ}\text{C}$		TYP.	2.5	μs
t_{off}				25	
V_{CL}	$I_{CL}=0.1\text{mA } t_p=1\text{ms}$		MIN.	950	V

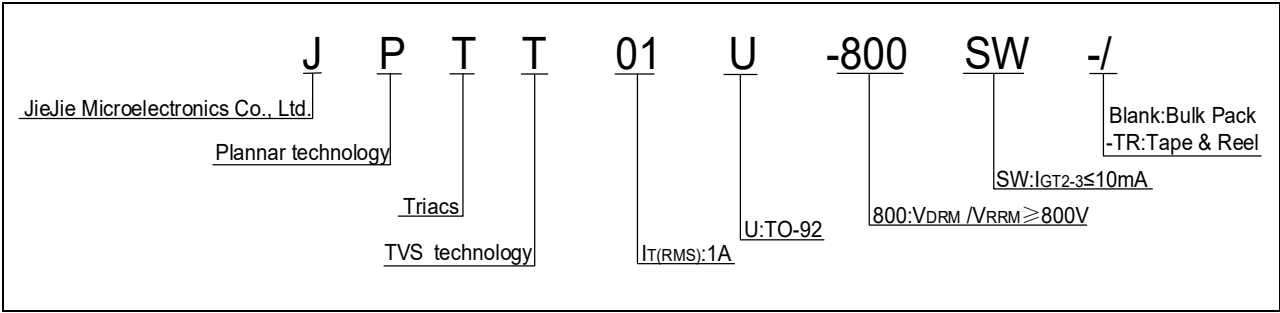
STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX.)	Unit
V_{TM}	$I_{TM}=1.1\text{A } t_p=380\mu\text{s}$	$T_j=25^{\circ}\text{C}$	1.34	V
V_{TO}	Threshold voltage	$T_j=125^{\circ}\text{C}$	0.79	V
R_D	Dynamic resistance	$T_j=125^{\circ}\text{C}$	429	$\text{m}\Omega$
I_{DRM}	$V_D=V_{DRM} V_R=V_{RRM}$	$T_j=25^{\circ}\text{C}$	2	μA
I_{RRM}		$T_j=125^{\circ}\text{C}$	0.2	mA

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	junction to case (AC)	55	$^{\circ}\text{C}/\text{W}$
$R_{th(j-a)}$	junction to ambient (AC)	150	$^{\circ}\text{C}/\text{W}$

ORDERING INFORMATION



MARKING

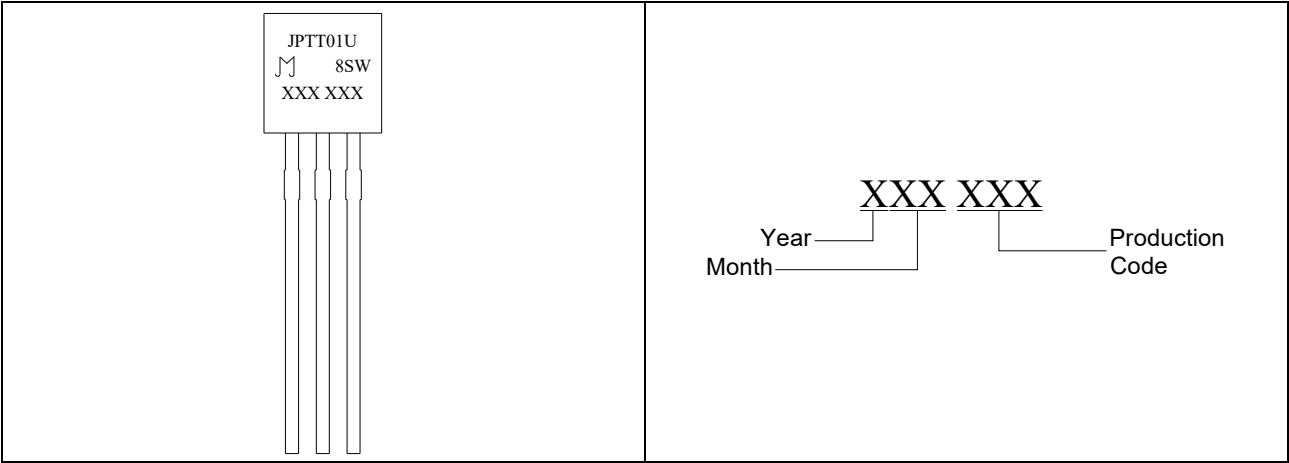


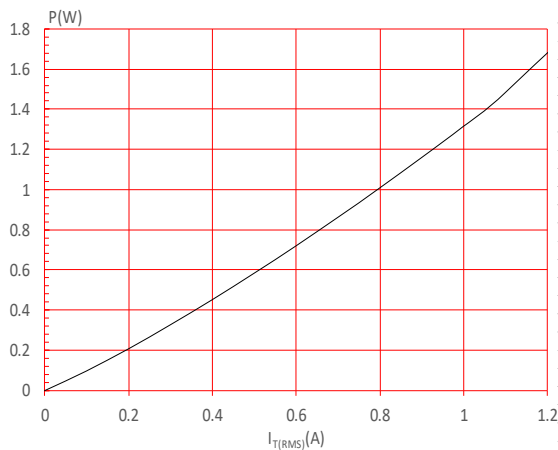
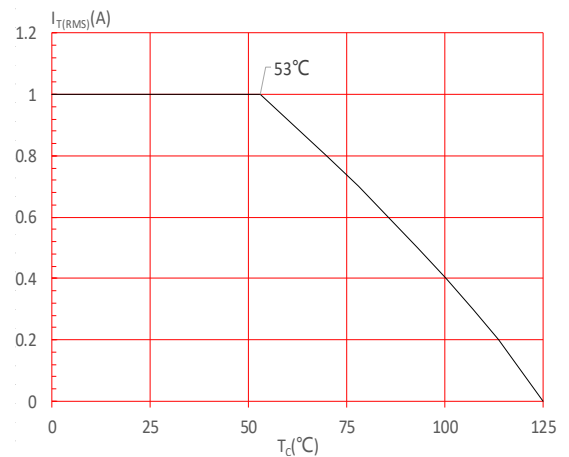
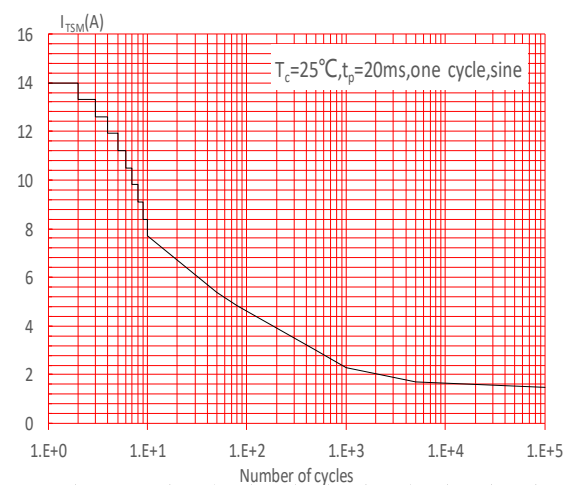
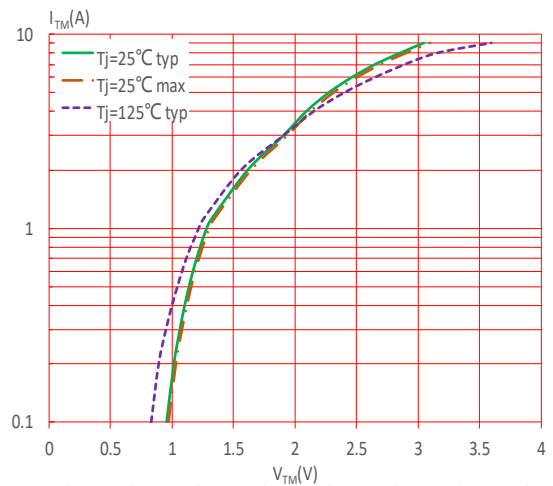
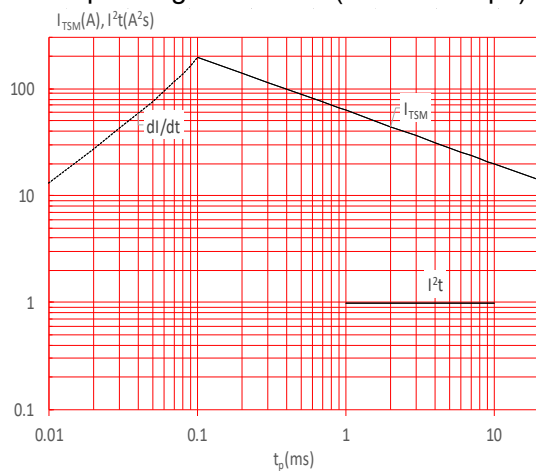
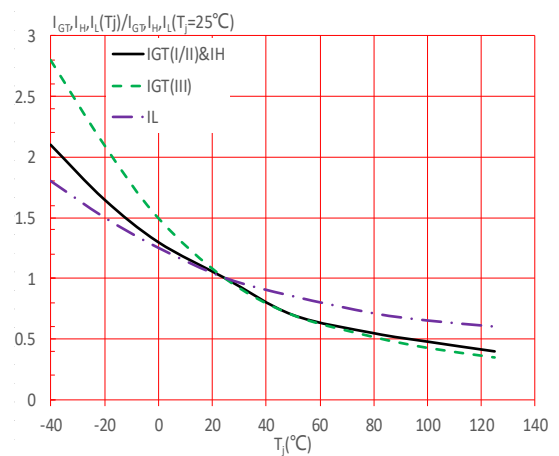
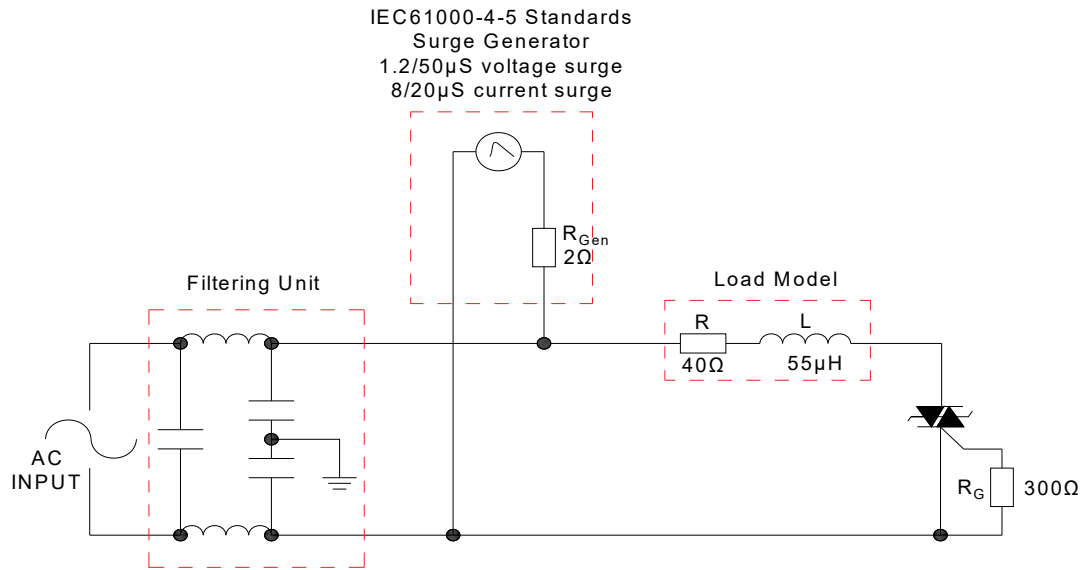
FIG.1: Maximum power dissipation versus RMS on-state current**FIG.2:** RMS on-state current versus case temperature**FIG.3:** Surge peak on-state current versus number of cycles**FIG.4:** On-state characteristics**FIG.5:** Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 20ms$, and corresponding value of I^2t ($dI/dt < 100A/\mu s$)**FIG.6:** Relative variations of gate trigger current, holding current and latching current versus junction temperature

FIG.7: Test circuit for inductive and resistive loads to IEC-61000-4-5 standards



LEAD FORMING AND SOLDERING

Refer to the application note “Assembly Instructions for Thyristors in Through-hole Package” released by JieJie Microelectronics

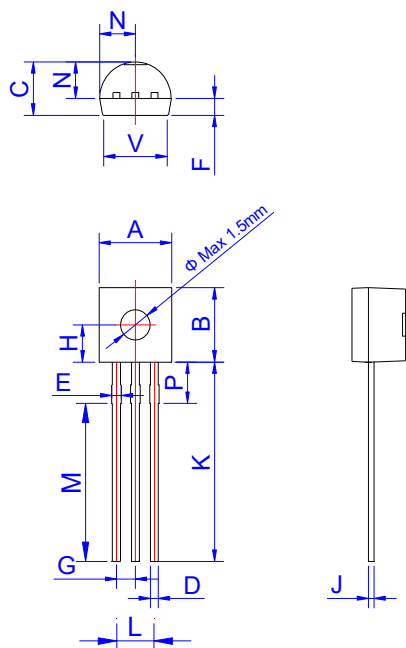
ORDERING INFORMATION

Order code	Voltage $V_{\text{DRM}}/V_{\text{RRM}}$ (V)	IGT(mA)	Package	Base qty. (pcs)	Delivery mode
JPTT01U-800SW	800	10	TO-92	1,000	Bulk Pack
JPTT01U-800SW-TR				2,000	Tape & Reel

Document Revision History

Date	Revision	Changes
Apr.10, 2023	A.1.0	Last updated
Mar.31, 2025	A.2.0	Renew PACKAGE MECHANICAL DATA
Sept.28, 2025	A.2.1	Revise PACKAGE MECHANICAL DATA

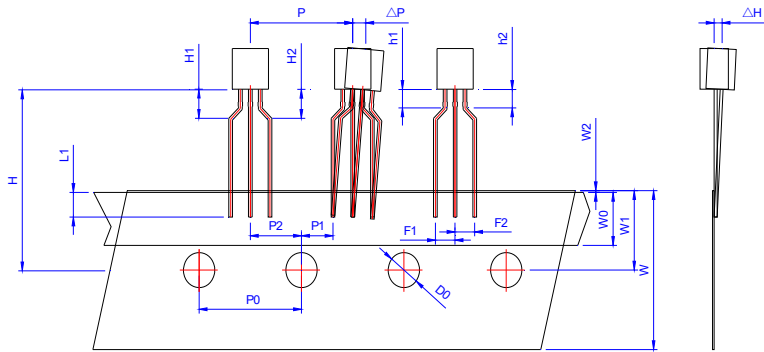
PACKAGE MECHANICAL DATA



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.45		5.20	0.175		0.205
B	4.32		5.33	0.170		0.210
C	3.18		4.19	0.125		0.165
D	0.407		0.533	0.016		0.021
E	0.50		0.70	0.020		0.028
F	1.10		1.30	0.043		0.051
G	1.10		1.40	0.043		0.055
H	2.20		2.40	0.087		0.094
J	0.36		0.50	0.014		0.020
K	12.70		15.0	0.500		0.591
L	2.44		2.64	0.096		0.104
M	11.64		12.04	0.458		0.474
N	2.04		2.66	0.080		0.105
P	1.80		2.30	0.071		0.091
V	4.10		4.50	0.161		0.177

DELIVERY MODE

PACKAGE	OUTLINE	BAG (PCS)	INNER BOX (PCS)	CARTON BOX (PCS)
TO-92	Bulk Pack	1,000	10,000	50,000



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
P	12.40	12.70	13.00	0.488	0.500	0.512
P0	12.40	12.70	13.00	0.488	0.500	0.512
P1	3.55	3.85	4.15	0.140	0.152	0.163
P2	5.95	6.35	6.75	0.233	0.250	0.265
ΔP	-1.00	0	1.00	-0.039	0	0.039
F1、F2	2.30	2.50	2.70	0.090	0.098	0.106
F1-F2	-0.10	0	0.10	-0.004	0	0.004
W	17.50	18.00	19.00	0.689	0.709	0.748
W0	5.50	6.00	6.50	0.217	0.236	0.256
W1	8.50	9.00	9.50	0.335	0.354	0.374
W2			1.00			0.039
D0	3.80	4.00	4.20	0.150	0.157	0.165
ΔH	-1.00	0	1.00	-0.039	0	0.039
L1	2.50			0.098		
H	18.00	19.00	20.00	0.709	0.748	0.787
H1、H2			3.00			0.119
H1-H2	-0.50		0.50	-0.020		0.020
h1、h2			1.00			0.040
h1-h2	-0.20		0.20	-0.008		0.008

PACKAGE	OUTLINE	REEL (PCS)	INNER BOX (PCS)	CARTON BOX (PCS)
TO-92	Tape & Reel	/	2,000	20,000

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